

Amendments To The Claims:

1. (Previously presented) A polishing composition used in precision polishing a wafer surface, the polishing composition comprising:

colloidal silica, wherein an average primary particle diameter D_{SA} of the colloidal silica, which is obtained from a specific surface area of the colloidal silica measured by a BET method, is from 5 to 30 nm; wherein an average secondary particle diameter D_{N4} of the colloidal silica, which is measured by a laser scattering method, is from 5 to 120 nm;

an alkaline compound, wherein the alkaline compound is ammonia;

a water-soluble polymer; and

water.

2. (Previously presented) The polishing composition according to claim 1, wherein the average primary particle diameter D_{SA} of the colloidal silica is from 5 to 25 nm.

3. (Previously presented) The polishing composition according to claim 2, wherein the average primary particle diameter D_{SA} of the colloidal silica is from 5 to 20 nm.

4. (Original) The polishing composition according to claim 1, wherein the average secondary particle diameter D_{N4} of the colloidal silica is from 5 to 100 nm.

5. (Original) The polishing composition according to claim 4, wherein the average secondary particle diameter D_{N4} of the colloidal silica is from 5 to 80 nm.

6. (Canceled)

7. (Original) The polishing composition according to claim 1, wherein the water-soluble polymer is at least one selected from hydroxyethyl cellulose, polyvinyl alcohol, and polyethylene oxide.

8. (Original) The polishing composition according to claim 7, wherein the water-soluble

polymer is hydroxyethyl cellulose.

9. (Original) The polishing composition according to claim 8, wherein content of the hydroxyethyl cellulose in the polishing composition is from 0.005 to 1.5 wt%.

10. (Canceled)

11 (Withdrawn – Previously presented) A method of polishing a wafer, the method comprising:

preparing a polishing composition, wherein the polishing composition includes:

colloidal silica,

wherein an average primary particle diameter D_{SA} of the colloidal silica, which is obtained from a specific surface area of the colloidal silica measured by a BET method, is from 5 to 30 nm; wherein an average secondary particle diameter D_{N4} of the colloidal silica, which is measured by a laser scattering method, is from 5 to 120 nm;

an alkaline compound, wherein the alkaline compound is ammonia;

a water-soluble polymer; and

water; and

precision polishing a surface of the wafer using the polishing composition.

12-17. (Canceled)

18. (Previously presented) The polishing composition according to claim 1, wherein the content of colloidal silica in the polishing composition is from 0.1 to 40 wt%.

19. (Previously presented) The polishing composition according to claim 1, wherein the content of colloidal silica in the polishing composition is from 0.1 to 1 wt%.

20. (Previously presented) The polishing composition according to claim 8, wherein the content of the hydroxyethyl cellulose in the polishing composition is from 0.05 to 0.5 wt%.

21. (Previously presented) The polishing composition according to claim 8, wherein the average molecular weight of the hydroxyethyl cellulose is from 300,000 to 3,000,000.

22. (Previously presented) The polishing composition according to claim 1, wherein the content of the alkaline compound in the polishing composition is from 0.01 to 8 wt%.

23. (Previously presented) The polishing composition according to claim 22, wherein the content of the alkaline compound in the polishing composition is from 0.1 to 3 wt%.

24-27. (Canceled)

28. (Previously presented) A polishing composition used in precision polishing a wafer surface, the polishing composition comprising:

colloidal silica, wherein an average primary particle diameter D_{SA} of the colloidal silica, which is obtained from a specific surface area of the colloidal silica measured by a BET method, is from 5 to 20 nm, wherein an average secondary particle diameter D_{N4} of the colloidal silica, which is measured by a laser scattering method, is from 5 to 80 nm, and wherein the content of colloidal silica in the polishing composition is from 0.1 to 40 wt%;

an alkaline compound, wherein the alkaline compound is ammonia;

a water-soluble polymer, wherein the water-soluble polymer is at least one selected from hydroxyethyl cellulose, polyvinyl alcohol, and polyethylene oxide; and

water.